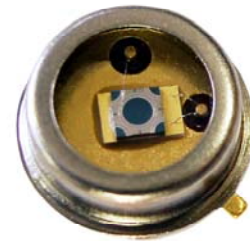


AD1100-8 TO5i

Avalanche Photodiode

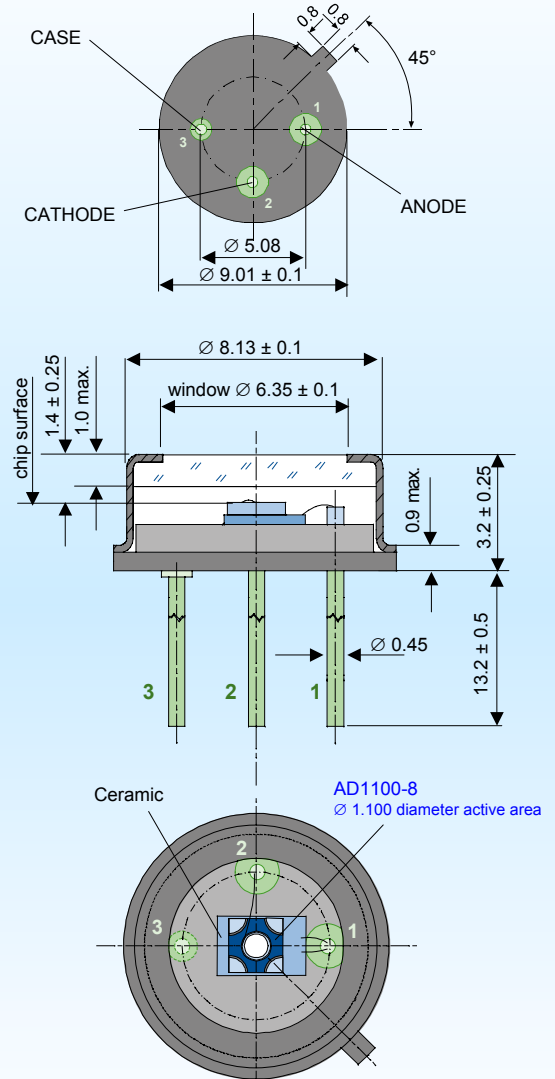
Special characteristics:

high gain at low bias voltage
fast rise time
1130 μm diameter active area
low capacitance



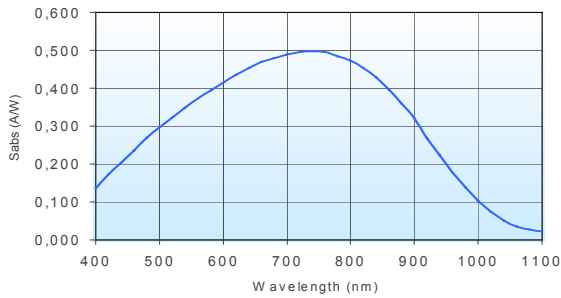
Parameters:	AD1100-8 TO5i
Active Area	1.0 mm ² Ø 1130 μm
Dark Current ¹⁾ (M = 100)	max. 10 nA typ. 4 ... 6 nA
Total Capacitance ¹⁾ (M = 100)	typ. 8 pF
Breakdown Voltage U _{BR} (at I _D = 2 μA)	90 ... 240 V typ. 120 ... 190 V
Temperature Coefficient of U _{BR}	typ. 0.45 V/K
Spectral Responsivity ¹⁾ (at 800 nm, M = 100)	min. 45 A/W typ. 50 A/W
Cut-off Frequency (-3dB)	typ. 0.35 GHz
Rise Time at 905 nm, 50 Ω	typ. 1.0 ns
Optimum Gain	40 - 60
Max. Gain	> 200
"Excess Noise" factor (M = 100)	typ. 2.2
"Excess Noise" index (M = 100)	typ. 0.2
N.E.P. (M = 100, 800 nm)	typ. 8* 10 ⁻¹⁴ W/Hz ^{1/2}
Operating Temperature	-20 ... +70 °C
Storage Temperature	-60 ... +100 °C
1) measurement conditions: Setup of photo current 10 nA at M = 1 and irradiation by a LED (680 nm, 60 nm bandwidth). Increase the photo current up to 1 μA , (M = 100) by internal multiplication due to an increasing bias voltage	

Package 3 (TO5i):



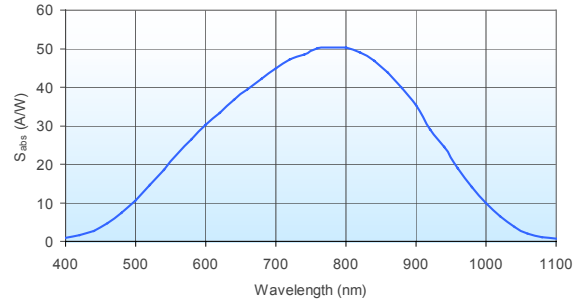
Spectral Responsivity at M=1

series - 8



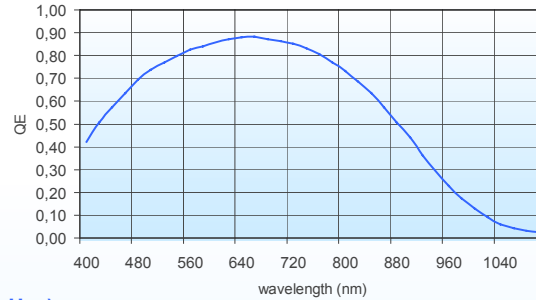
Spectral Responsivity at M=100

series - 8



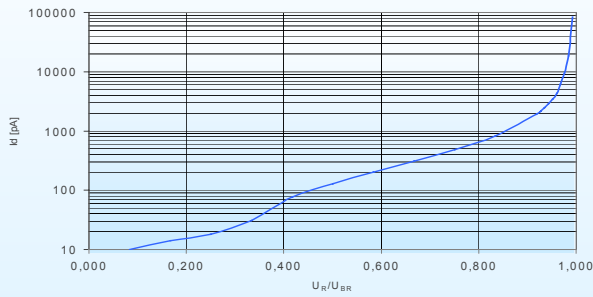
Quantum Efficiency for M = 100

series - 8



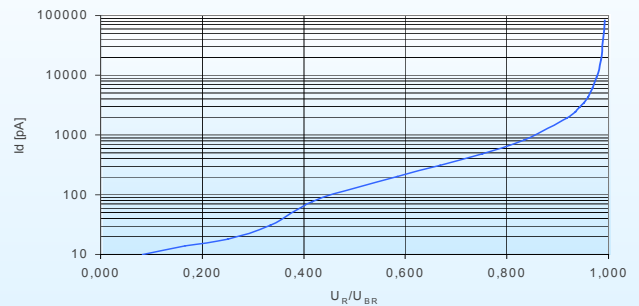
$$I_D = f(U_R/U_{BR})$$

AD1100-8



$$M = f(U_R/U_{BR})$$

AD1100-8



Maximum Ratings:

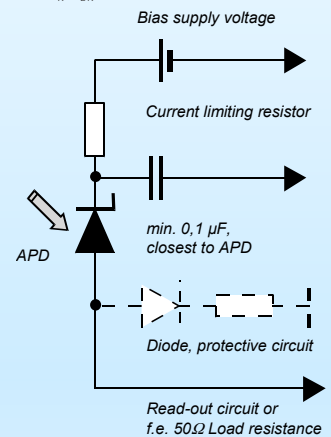
- max. electrical power dissipation 100 mW at 22°C
- max. optical peak value, once 200 mW for 1 s
- max. continuous optical operation $I_{ph} (DC) \leq 250 \mu A$
 $\leq 1 \text{ mA}$ for signal 50 μs "on" / 1 ms "off"
- $(P_{electr.} = P_{opt.} * S_{abs} * M * U_R)$

Application Hints:

- Current should be limited by a protecting resistor or current limiting - IC inside the power supply.
- Use of low noise read-out - IC.
- For high gain applications bias voltage should be temperature compensated.
- For low light level applications, blocking of ambient light should be used.

Handling Precautions:

- Soldering temperature 260 °C for max. 10 s. The device must be protected against solder flux vapour!
- min. Pin - length 2 mm
- ESD - protection Standard precautionary measures are sufficient.
- Storage Store devices in conductive foam.
- Avoid skin contact with window!
- Clean window with Ethyl alcohol if necessary.
- Do not scratch or abrade window.



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